

# Yuzo Shigesato

## List of Publications by Year in descending order

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166  
papers

5,384  
citations

70961

41  
h-index

102304

66  
g-index

172  
all docs

172  
docs citations

172  
times ranked

4279  
citing authors

#	ARTICLE	IF	CITATIONS
1	ITO/AgPd/ITO Laminated Films for High-performance Transparent Thin Film Heaters. Vacuum and Surface Science, 2022, 65, 84-89.	0.0	0
2	How mass disorder affects heat conduction in ternary amorphous alloys. AIP Advances, 2021, 11, 065026.	0.6	1
3	Temporal Evolution of Microscopic Structure and Functionality during Crystallization of Amorphous Indium-Based Oxide Films. ACS Applied Materials & Interfaces, 2021, 13, 31825-31834.	4.0	9
4	Thermal conductivity across the van der Waals layers of $\text{In}_2\text{S}_3$ -MoO <sub>3</sub> thin films composed of mosaic domains with in-plane 90° rotations. Journal of Applied Physics, 2021, 130, .	1.1	4
5	p-type conduction mechanism in continuously varied non-stoichiometric SnO <sub>x</sub> thin films deposited by reactive sputtering with the impedance control. Journal of Applied Physics, 2020, 127, 185703.	1.1	12
6	Carrier densities of Sn-doped In <sub>2</sub> O <sub>3</sub> nanoparticles and their effect on X-ray photoelectron emission. Journal of Applied Physics, 2019, 125, 245303.	1.1	6
7	Deposition of TiO <sub>2</sub> photocatalyst on polyethylene terephthalate or polyimide polymer films by reactive sputtering for flexible photocatalytic sheets. Japanese Journal of Applied Physics, 2019, 58, 055503.	0.8	2
8	Thermal conductivity of hetero-epitaxial ZnO thin films on <i>c</i> - and <i>r</i> -plane sapphire substrates: Thickness and grain size effect. Journal of Applied Physics, 2019, 125, .	1.1	31
9	How the sputtering process influence structural, optical, and electrical properties of Zn <sub>3</sub> N <sub>2</sub> films?. MRS Communications, 2018, 8, 314-321.	0.8	3
10	Geometric structure of Sn dopants in sputtered TiO <sub>2</sub> film revealed by x-ray absorption spectroscopy and first-principles DFT calculations. Materials Research Express, 2018, 5, 046412.	0.8	4
11	Evolution of Defect Structures and Deep Subgap States during Annealing of Amorphous In-Ga-Zn Oxide for Thin-Film Transistors. Physical Review Applied, 2018, 9, .	1.5	25
12	Photocatalytic oxidation of benzene in a microreactor with immobilized TiO <sub>2</sub> thin films deposited by sputtering. Catalysis Communications, 2017, 100, 1-4.	1.6	9
13	A visible-light active TiO <sub>2</sub> photocatalyst multilayered with WO <sub>3</sub> . Physical Chemistry Chemical Physics, 2017, 19, 17342-17348.	1.3	23
14	Structure and thermophysical properties of GaN films deposited by reactive sputtering using a metal Ga target. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	11
15	Indium oxide-based transparent conductive films deposited by reactive sputtering using alloy targets. Japanese Journal of Applied Physics, 2017, 56, 045503.	0.8	6
16	Effect of nitrogen addition on the structural, electrical, and optical properties of In-Sn-Zn oxide thin films. Applied Surface Science, 2017, 396, 897-901.	3.1	14
17	Formation of homologous In <sub>2</sub> O <sub>3</sub> (ZnO) <sub>m</sub> thin films and its thermoelectric properties. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 041507.	0.9	4
18	Crystallization behavior of amorphous indium-gallium-zinc-oxide films and its effects on thin-film transistor performance. Japanese Journal of Applied Physics, 2016, 55, 035504.	0.8	21

#	ARTICLE	IF	CITATIONS
19	On the Crystal Structural Control of Sputtered TiO <sub>2</sub> Thin Films. <i>Nanoscale Research Letters</i> , 2016, 11, 324.	3.1	30
20	Influence of dopant species and concentration on grain boundary scattering in degenerately doped In <sub>2</sub> O <sub>3</sub> thin films. <i>Thin Solid Films</i> , 2016, 614, 62-68.	0.8	40
21	Crystallization behavior during transparent In <sub>2</sub> O <sub>3</sub> /ZnO film growth. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 2291-2295.	0.8	5
22	Comparative study of sputter-deposited SnO <sub>2</sub> films doped with antimony or tantalum. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 923-928.	0.7	18
23	Tailoring the crystal structure of TiO <sub>2</sub> thin films from the anatase to rutile phase. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	12
24	Amorphous indium-tin-zinc oxide films deposited by magnetron sputtering with various reactive gases: Spatial distribution of thin film transistor performance. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	23
25	Comparison of CF <sub>4</sub> and C <sub>4</sub> F <sub>8</sub> gas etching profiles by multiscale simulation. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 036501.	0.8	6
26	Temperature dependence of thermal conductivity of VO <sub>2</sub> thin films across metal-insulator transition. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 053201.	0.8	65
27	Visible-light active thin-film WO <sub>3</sub> photocatalyst with controlled high-rate deposition by low-damage reactive-gas-flow sputtering. <i>APL Materials</i> , 2015, 3, 104407.	2.2	23
28	Tuning hole charge collection efficiency in polymer photovoltaics by optimizing the work function of indium tin oxide electrodes with solution-processed LiF nanoparticles. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 9205-9212.	1.1	6
29	Origin of carrier scattering in polycrystalline Al-doped ZnO films. <i>Applied Physics Express</i> , 2014, 7, 105802.	1.1	28
30	Thermophysical properties of SnO <sub>2</sub> -based transparent conductive films: Effect of dopant species and structure compared with In <sub>2</sub> O <sub>3</sub> -, ZnO-, and TiO <sub>2</sub> -based films. <i>Journal of Materials Research</i> , 2014, 29, 1579-1584.	1.2	13
31	Transparent conductive Al and Ga doped ZnO films deposited using off-axis sputtering. <i>Thin Solid Films</i> , 2014, 559, 69-77.	0.8	21
32	Al-doped ZnO films deposited on a slightly reduced buffer layer by reactive dc unbalanced magnetron sputtering. <i>Thin Solid Films</i> , 2014, 555, 93-99.	0.8	22
33	Transparent conductive Nb-doped TiO <sub>2</sub> films deposited by reactive dc sputtering using Ti-Nb alloy target, precisely controlled in the transition region using impedance feedback system. <i>Applied Surface Science</i> , 2014, 301, 551-556.	3.1	24
34	Study on reactive sputtering to deposit transparent conductive amorphous In <sub>2</sub> O <sub>3</sub> /ZnO films using an In-Zn alloy target. <i>Thin Solid Films</i> , 2014, 559, 49-52.	0.8	8
35	Effect of Nb Concentration on Thermal Diffusivity of Nb-Doped TiO <sub>2</sub> Films. <i>Netsu Bussei</i> , 2014, 25, 117-120.	0.1	2
36	Direct observation of the band gap shrinkage in amorphous In <sub>2</sub> O <sub>3</sub> /ZnO thin films. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	20

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37	Thermal Conductivity of Amorphous Indium-Gallium-Zinc Oxide Thin Films. Applied Physics Express, 2013, 6, 021101.	1.1	59
38	Early Stages of Sn-Doped In <sub>2</sub> O <sub>3</sub> Film Growth on Amorphous SiO <sub>2</sub> Surfaces Observed by Atomic Force Microscopy and Transmission Electron Microscopy. Japanese Journal of Applied Physics, 2013, 52, 128007.	0.8	0
39	Thermal Boundary Resistance of W/Al <sub>2</sub> O <sub>3</sub> Interface in W/Al <sub>2</sub> O <sub>3</sub> /W Three-Layered Thin Film and Its Dependence on Morphology. Japanese Journal of Applied Physics, 2013, 52, 065802.	0.8	15
40	<i>In situ</i> analyses on negative ions in the indium-gallium-zinc oxide sputtering process. Applied Physics Letters, 2013, 103, .	1.5	31
41	Annealing Effects on Ta Doped SnO <sub>2</sub> Films. Materials Research Society Symposia Proceedings, 2012, 1454, 245-251.	0.1	0
42	Photocatalytic Activity of WO <sub>3</sub> Films Crystallized by Postannealing in Air. Japanese Journal of Applied Physics, 2012, 51, 055501.	0.8	9
43	Visible light-induced photocatalytic properties of WO <sub>3</sub> films deposited by dc reactive magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	0.9	19
44	Thermophysical and electrical properties of Al-doped ZnO films. Journal of Applied Physics, 2012, 111, .	1.1	27
45	Visible-Light Active Photocatalytic WO <sub>3</sub> Films Loaded with Pt Nanoparticles Deposited by Sputtering. Journal of Nanoscience and Nanotechnology, 2012, 12, 5082-5086.	0.9	20
46	Electronic State of Amorphous Indium Gallium Zinc Oxide Films Deposited by DC Magnetron Sputtering with Water Vapor Introduction. Applied Physics Express, 2012, 5, 075802.	1.1	24
47	Thermophysical Properties of Transparent Conductive Nb-Doped TiO <sub>2</sub> Films. Japanese Journal of Applied Physics, 2012, 51, 035802.	0.8	19
48	Experimental observation on the Fermi level shift in polycrystalline Al-doped ZnO films. Journal of Applied Physics, 2012, 112, .	1.1	83
49	High-rate deposition of high-quality Sn-doped In <sub>2</sub> O <sub>3</sub> films by reactive magnetron sputtering using alloy targets. Thin Solid Films, 2012, 520, 4101-4105.	0.8	18
50	In-situ analyses on the reactive sputtering process to deposit Al-doped ZnO films using an Al-Zn alloy target. Thin Solid Films, 2012, 520, 3751-3754.	0.8	16
51	Photocatalytic Activity of WO <sub>3</sub> Films Crystallized by Postannealing in Air. Japanese Journal of Applied Physics, 2012, 51, 055501.	0.8	4
52	Thermophysical Properties of Transparent Conductive Nb-Doped TiO <sub>2</sub> Films. Japanese Journal of Applied Physics, 2012, 51, 035802.	0.8	5
53	Oxidation Resistance of Ti-Al-N and Ti-Al-Si-N Films Deposited by Reactive Sputtering Using Alloy Targets. Japanese Journal of Applied Physics, 2011, 50, 075802.	0.8	1
54	In-situ analysis of positive and negative energetic ions generated during Sn-doped In <sub>2</sub> O <sub>3</sub> deposition by reactive sputtering. Thin Solid Films, 2011, 520, 1182-1185.	0.8	9

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55	High-rate deposition of Sb-doped SnO <sub>2</sub> films by reactive sputtering using the impedance control method. Thin Solid Films, 2011, 520, 1178-1181.	0.8	21
56	Effect of Oxygen Impurities on Thermal Diffusivity of AlN Thin Films Deposited by Reactive RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2011, 50, 11RB01.	0.8	5
57	Thermal Boundary Resistance between N,N'-Bis(1-naphthyl)-N,N'-diphenylbenzidine and Aluminum Films. Japanese Journal of Applied Physics, 2011, 50, 11RB02.	0.8	0
58	Thermal Conductivity of Amorphous Indium Zinc Oxide Thin Films. Materials Research Society Symposia Proceedings, 2011, 1315, 1.	0.1	2
59	High Rate Reactive Sputter Deposition of TiO <sub>2</sub> Films for Photocatalyst and Dye-Sensitized Solar Cells. Japanese Journal of Applied Physics, 2011, 50, 045802.	0.8	0
60	In Based TCOs. , 2011, , 149-169.		2
61	High Rate Reactive Sputter Deposition of TiO <sub>2</sub> Films for Photocatalyst and Dye-Sensitized Solar Cells. Japanese Journal of Applied Physics, 2011, 50, 045802.	0.8	4
62	Oxidation Resistance of TiN and AlN Films Deposited by Reactive Sputtering Using Alloy Targets. Japanese Journal of Applied Physics, 2011, 50, 075802.	0.8	8
63	Effect of Oxygen Impurities on Thermal Diffusivity of AlN Thin Films Deposited by Reactive RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2011, 50, 11RB01.	0.8	7
64	Thermal Boundary Resistance between N,N'-Bis(1-naphthyl)-N,N'-diphenylbenzidine and Aluminum Films. Japanese Journal of Applied Physics, 2011, 50, 11RB02.	0.8	3
65	DC sputter deposition of amorphous indium gallium zinc oxide (a-IGZO) films with H <sub>2</sub> O introduction. Thin Solid Films, 2010, 518, 3004-3007.	0.8	46
66	Al-doped ZnO (AZO) films deposited by reactive sputtering with unipolar-pulsing and plasma-emission control systems. Thin Solid Films, 2010, 518, 2980-2983.	0.8	33
67	Thermophysical properties of aluminum oxide and molybdenum layered films. Thin Solid Films, 2010, 518, 3119-3121.	0.8	42
68	Carrier Density Dependence of Optical Band Gap and Work Function in Sn-Doped In <sub>2</sub> O <sub>3</sub> Films. Applied Physics Express, 2010, 3, 061101.	1.1	38
69	High-Performance and High-CRI OLEDs for Lighting and Their Fabrication Processes. Advances in Science and Technology, 2010, 75, 65-73.	0.2	6
70	Spatial distribution of electrical properties for Al-doped ZnO films deposited by dc magnetron sputtering using various inert gases. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 895-900.	0.9	16
71	High rate reactive magnetron sputter deposition of Al-doped ZnO with unipolar pulsing and impedance control system. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 890-894.	0.9	17
72	Study on MoO <sub>3</sub> films deposited by reactive sputtering for organic light-emitting diodes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 886-889.	0.9	23

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73	Thermal Diffusivities of Tris(8-hydroxyquinoline)aluminum and N,N'-Di(1-naphthyl)-N,N'-diphenylbenzidine Thin Films with Sub-Hundred Nanometer Thicknesses. Japanese Journal of Applied Physics, 2010, 49, 121602.	0.8	14
74	In-situ Analyses on Reactive Sputtering Processes to Deposit Photocatalytic TiO <sub>2</sub> Films. Japanese Journal of Applied Physics, 2010, 49, 041105.	0.8	11
75	Effects of Energetic Ion Bombardment on Structural and Electrical Properties of Al-Doped ZnO Films Deposited by RF-Superimposed DC Magnetron Sputtering. Japanese Journal of Applied Physics, 2010, 49, 071103.	0.8	44
76	Electrical and optical properties of Nb-doped TiO <sub>2</sub> films deposited by dc magnetron sputtering using slightly reduced Nb-doped TiO <sub>2-x</sub> ceramic targets. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 851-855.	0.9	36
77	<i>In situ</i> analyses on negative ions in the sputtering process to deposit Al-doped ZnO films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 846-850.	0.9	34
78	Sputter deposition of Al-doped ZnO films with various incident angles. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1166-1171.	0.9	28
79	Electrical and optical properties of Al-doped ZnO films deposited by hollow cathode gas flow sputtering. Thin Solid Films, 2009, 517, 3048-3052.	0.8	27
80	Study on inverse spinel zinc stannate, Zn <sub>2</sub> SnO <sub>4</sub> , as transparent conductive films deposited by rf magnetron sputtering. Thin Solid Films, 2009, 518, 1304-1308.	0.8	44
81	Thermal transport properties of polycrystalline tin-doped indium oxide films. Journal of Applied Physics, 2009, 105, .	1.1	103
82	Electrochromic Properties of Li <sub>x</sub> Ni <sub>y</sub> O Films Deposited by RF Magnetron Sputtering. Journal of the Electrochemical Society, 2009, 156, H629.	1.3	29
83	Transmission Electron Microscopy Observation on the Early Stages of Sn-Doped In <sub>2</sub> O <sub>3</sub> Film Growth Deposited on Amorphous Carbon Films by DC Magnetron Sputtering. Applied Physics Express, 2009, 2, 095501.	1.1	2
84	Comparative study on early stages of film growth for transparent conductive oxide films deposited by dc magnetron sputtering. Thin Solid Films, 2008, 516, 4598-4602.	0.8	40
85	Study on early stages of film growth for Sn doped In <sub>2</sub> O <sub>3</sub> films deposited at various substrate temperatures. Thin Solid Films, 2008, 516, 5868-5871.	0.8	23
86	Transparent conductive Nb-doped TiO <sub>2</sub> films deposited by direct-current magnetron sputtering using a TiO <sub>2-x</sub> target. Thin Solid Films, 2008, 516, 5758-5762.	0.8	130
87	Nb-doped TiO <sub>2</sub> films for transparent conductive electrodes with low resistivity deposited by dc magnetron sputtering using a TiO <sub>2-x</sub> Nb <sub>2</sub> O <sub>5-x</sub> target. Materials Research Society Symposia Proceedings, 2008, 1109, 32601.	0.1	0
88	High rate deposition of photocatalytic TiO <sub>2</sub> films by dc magnetron sputtering using a TiO <sub>2-x</sub> target. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 903-907.	0.9	12
89	High rate deposition of photocatalytic TiO <sub>2</sub> films with high activity by hollow cathode gas-flow sputtering method. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 893-897.	0.9	13
90	High rate deposition of photocatalytic TiO <sub>2</sub> films with high activity by hollow cathode gas-flow sputtering method. Journal of the Vacuum Society of Japan, 2008, 51, 111-117.		

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91	Novel emission properties of melem caused by the heavy metal effect of lanthanides(iii) in a LB film. Photochemical and Photobiological Sciences, 2007, 6, 804.	1.6	13
92	Structure and Internal Stress of Tin-Doped Indium Oxide and Indium-Zinc Oxide Films Deposited by DC Magnetron Sputtering. Japanese Journal of Applied Physics, 2007, 46, 7806-7811.	0.8	30
93	Molecular Distortion Effect on ff-Emission in a Pr(III) Complex with 4,7-Diphenyl-1,10-Phenanthroline. ChemPhysChem, 2007, 8, 1345-1351.	1.0	11
94	Study on Relationships between Internal Stress and Photodecomposition Properties of Thin Film Titanium Dioxide Photocatalyst. Shinku/Journal of the Vacuum Society of Japan, 2007, 50, 432-436.	0.2	0
95	Assembled structures of nanocrystals in polymer/calcium carbonate thin-film composites formed by the cooperation of chitosan and poly(aspartate). Journal of Polymer Science Part A, 2006, 44, 5153-5160.	2.5	48
96	Excitation energy transfer between D3h melamines and Pr(III) in the solid state. Science and Technology of Advanced Materials, 2006, 7, 72-76.	2.8	12
97	Structural, electrical, and optical properties of transparent conductive In <sub>2</sub> O <sub>3</sub> -SnO <sub>2</sub> films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1167-1172.	0.9	51
98	Analysis on thermal properties of tin doped indium oxide films by picosecond thermoreflectance measurement. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 1180-1186.	0.9	79
99	Structures and Electrical Properties of Tin Doped Indium Oxide (ITO) Films Deposited on Different Substrates by Sputtering with H <sub>2</sub> O Introduction. Shinku/Journal of the Vacuum Society of Japan, 2004, 47, 796-801.	0.2	3
100	Crystallinity and Photocatalytic Activity of TiO <sub>2</sub> Films Deposited by Reactive Sputtering Using Various Magnetic Field Strengths. Japanese Journal of Applied Physics, 2004, 43, L442-L445.	0.8	41
101	Photocatalytic Properties of TiO <sub>2</sub> Films Deposited by Reactive Sputtering in Mid-Frequency Mode with Dual Cathodes. Japanese Journal of Applied Physics, 2004, 43, 8234-8241.	0.8	32
102	GaN Films Deposited by DC Reactive Magnetron Sputtering. Japanese Journal of Applied Physics, 2004, 43, L164-L166.	0.8	10
103	Crystal Structure and Photocatalytic Activity of TiO <sub>2</sub> Films Deposited by Reactive Sputtering Using Ne, Ar, Kr, or Xe Gases. Japanese Journal of Applied Physics, 2004, 43, L358-L361.	0.8	35
104	Metallization in a-Si:H TFT Array Fabrication - Deposition and Wet Etching of Conductors. , 2004, , 313-376.		3
105	High Rate Depositions of Transparent Conductive Al-doped ZnO Films by Reactive Sputtering. Shinku/Journal of the Vacuum Society of Japan, 2004, 47, 727-733.	0.2	1
106	Thin film TiO <sub>2</sub> photocatalyst deposited by reactive magnetron sputtering. Thin Solid Films, 2003, 442, 227-231.	0.8	185
107	Study on Thermochromic VO <sub>2</sub> Films Grown on ZnO-Coated Glass Substrates for "Smart Windows". Japanese Journal of Applied Physics, 2003, 42, 6523-6531.	0.8	68
108	Impedance Control of Reactive Sputtering Process in Mid-Frequency Mode with Dual Cathodes to Deposit Al-Doped ZnO Films. Japanese Journal of Applied Physics, 2003, 42, 263-269.	0.8	44



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109	Photoinduced Hydrophilicity of Epitaxially Grown TiO <sub>2</sub> Films by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2003, 42, L1529-L1531.	0.8	22
110	Crystallinity of Gallium-Doped Zinc Oxide Films Deposited by DC Magnetron Sputtering Using Ar, Ne or Kr Gas. Japanese Journal of Applied Physics, 2002, 41, 6174-6179.	0.8	45
111	Al-Doped ZnO Films Deposited by Reactive Magnetron Sputtering in Mid-Frequency Mode with Dual Cathodes. Japanese Journal of Applied Physics, 2002, 41, 814-819.	0.8	55
112	Thermochromic VO <sub>2</sub> Films Heteroepitaxially Grown on ZnO Coated Glass by RF Sputtering. Materials Research Society Symposia Proceedings, 2001, 666, 1041.	0.1	1
113	Microstructure of Heteroepitaxially Grown TiO <sub>2</sub> Films by Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2001, 672, 1.	0.1	4
114	Thermochromic nondoped and W-doped VO <sub>2</sub> films heteroepitaxially grown on glass substrate using ZnO polycrystalline films as buffer layers. , 2001, , .		2
115	Electronic Structure Analyses of Sn-doped In <sub>2</sub> O <sub>3</sub> . Japanese Journal of Applied Physics, 2001, 40, 3231-3235.	0.8	67
116	Study on Fluorine-Doped Indium Oxide Films Deposited by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 2000, 39, 6422-6426.	0.8	27
117	Donor Compensation and Carrier-Transport Mechanisms in Tin-doped In <sub>2</sub> O <sub>3</sub> Films Studied by Means of Conversion Electron <sup>119</sup> Sn Mössbauer Spectroscopy and Hall Effect Measurements. Japanese Journal of Applied Physics, 2000, 39, 4158-4163.	0.8	48
118	Interfacial stability of an indium tin oxide thin film deposited on Si and Si <sub>0.85</sub> Ge <sub>0.15</sub> . Journal of Applied Physics, 2000, 88, 3717-3724.	1.1	32
119	Electrical properties and surface morphology of heteroepitaxial-grown tin-doped indium oxide thin films deposited by molecular-beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1663-1667.	0.9	12
120	Thermochromic VO <sub>2</sub> Films Deposited by RF Magnetron Sputtering Using V <sub>2</sub> O <sub>3</sub> or V <sub>2</sub> O <sub>5</sub> Targets. Japanese Journal of Applied Physics, 2000, 39, 6016-6024.	0.8	75
121	Targets for High Rate Reactive Sputtering. ITO Deposition by Reactive dc Magnetron Sputtering with Ozone Introduction.. Shinku/Journal of the Vacuum Society of Japan, 2000, 43, 779-784.	0.2	1
122	Preparation and Crystallization of Tin-doped and Undoped Amorphous Indium Oxide Films Deposited by Sputtering. Japanese Journal of Applied Physics, 1999, 38, 5224-5226.	0.8	81
123	Influence of Unbalanced Magnetron and Penning Ionization for RF Reactive Magnetron Sputtering. Japanese Journal of Applied Physics, 1999, 38, 186-191.	0.8	6
124	Doping Mechanisms of Sn in In <sub>2</sub> O <sub>3</sub> Powder Studied Using <sup>119</sup> Sn Mössbauer Spectroscopy and X-Ray Diffraction. Japanese Journal of Applied Physics, 1999, 38, 2856-2862.	0.8	59
125	Electrical and Structural Properties of Tin-Doped Indium Oxide Films Deposited by DC Sputtering at Room Temperature. Japanese Journal of Applied Physics, 1999, 38, 2921-2927.	0.8	115
126	Persistent Spectral Hole Burning in Samarium and Aluminum Codoped Silica Films Prepared by RF Sputtering.. Journal of the Ceramic Society of Japan, 1999, 107, 494-496.	1.3	0



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127	Characterization of RF-Enhanced DC Sputtering to Deposit Tin-Doped Indium Oxide Thin Films. Japanese Journal of Applied Physics, 1998, 37, 6210-6214.	0.8	12
128	Effect of Sn Doping on the Crystal Growth of Indium Oxide Films. Japanese Journal of Applied Physics, 1998, 37, 6585-6586.	0.8	13
129	A time-resolved reflectivity study of the amorphous-to-crystalline transformation kinetics in dc-magnetron sputtered indium tin oxide. Journal of Applied Physics, 1998, 83, 145-154.	1.1	62
130	Study on Crystallinity of Tin-Doped Indium Oxide Films Deposited by DC Magnetron Sputtering. Japanese Journal of Applied Physics, 1998, 37, 1870-1876.	0.8	100
131	In Situ Observation of Adsorbed Heptylviologen Cation Radicals by Slab Optical Waveguide Spectroscopy Utilizing Indium-tin-oxide Electrode. Chemistry Letters, 1998, 27, 125-126.	0.7	30
132	Study on Electronic Structure and Optoelectronic Properties of Indium Oxide by First-Principles Calculations. Japanese Journal of Applied Physics, 1997, 36, 5551-5554.	0.8	72
133	Comparative study of heteroepitaxial and polycrystalline tin-doped indium oxide films. Journal of Non-Crystalline Solids, 1997, 218, 267-272.	1.5	25
134	Electrical properties of heteroepitaxial grown tin-doped indium oxide films. Journal of Applied Physics, 1996, 80, 978-984.	1.1	83
135	Structure Analysis of ZnO-TeO <sub>2</sub> Glasses by Means of Neutron Diffraction and Molecular Dynamics. Japanese Journal of Applied Physics, 1996, 35, 694-698.	0.8	18
136	Electronic Polarization in Mixed Alkali Silicate Glasses: A Molecular Dynamics Study. Japanese Journal of Applied Physics, 1996, 35, 2251-2252.	0.8	1
137	Origin of characteristic grain-subgrain structure of tin-doped indium oxide films. Thin Solid Films, 1995, 259, 38-45.	0.8	131
138	ITO thin-film transparent conductors: Microstructure and processing. Jom, 1995, 47, 47-50.	0.9	17
139	Effects of water partial pressure on the activated electron beam evaporation process to deposit tin-doped indium oxide films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 268-275.	0.9	27
140	Effects of Tin Concentrations on Structural Characteristics and Electrooptical Properties of Tin-Doped Indium Oxide Films Prepared by RF Magnetron Sputtering. Japanese Journal of Applied Physics, 1995, 34, 600-605.	0.8	27
141	Microstructure of Low-Resistivity Tin-Doped Indium Oxide Films Deposited at $150\text{ s}^{-1}$ . Japanese Journal of Applied Physics, 1995, 34, L244-L247.	0.8	51
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